BAS20HT1

Preferred Device

High Voltage Switching Diode

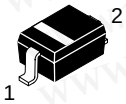
Features

- Pb−Free Package is Available

ON Semiconductor®

http://onsemi.com

HIGH VOLTAGE SWITCHING DIODE



SOD−323
CASE 477
STYLE 1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	200	Vdc
Repetitive Peak Reverse Voltage	V_{RRM}	200	Vdc
Peak Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	625	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board* T_A = 25°C Derate above 25°C	P_D	200 1.57	mW mW/°C
Thermal Resistance Junction−to−Ambient	$R_{\theta JA}$	635	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

*FR−5 Minimum Pad

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Voltage Leakage Current (V_R = 200 Vdc) (V_R = 200 Vdc, T_J = 150°C)	I_R	 − −	 1.0 100	μAdc
Reverse Breakdown Voltage (I_{BR} = 100 μAdc)	$V_{(BR)}$	250	−	Vdc
Forward Voltage (I_F = 100 mAdc) (I_F = 200 mAdc)	V_F	 − −	 1000 1250	mV
Diode Capacitance (V_R = 0, f = 1.0 MHz)	C_D	−	5.0	pF
Reverse Recovery Time (I_F = I_R = 30 mAdc, R_L = 100 Ω)	t_{rr}	−	50	ns

MARKING DIAGRAM

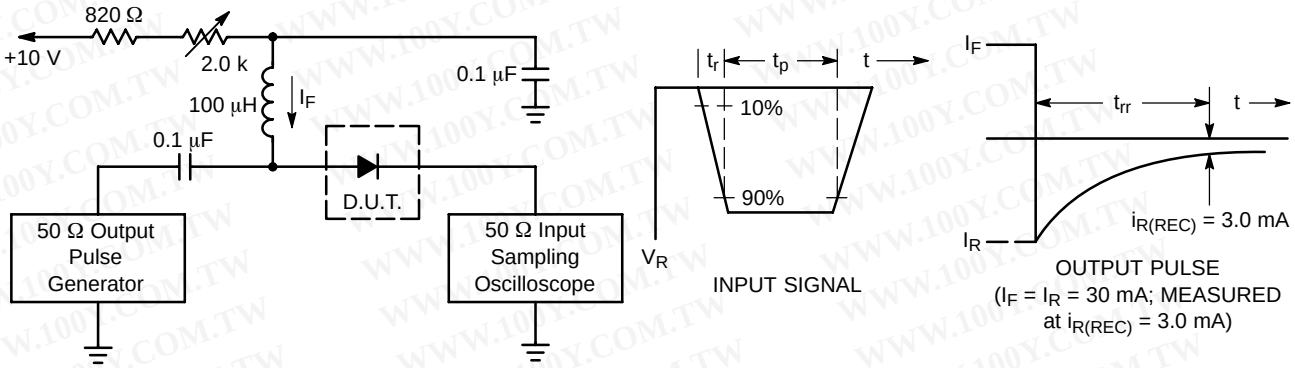
JR = Specific Device Code
M = Date Code*
▪ = Pb−Free Package
(Note: Microdot may be in either location)
*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BAS20HT1	SOD−323	3000/Tape & Reel
BAS20HT1G	SOD−323 (Pb−Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 30 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 30 mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

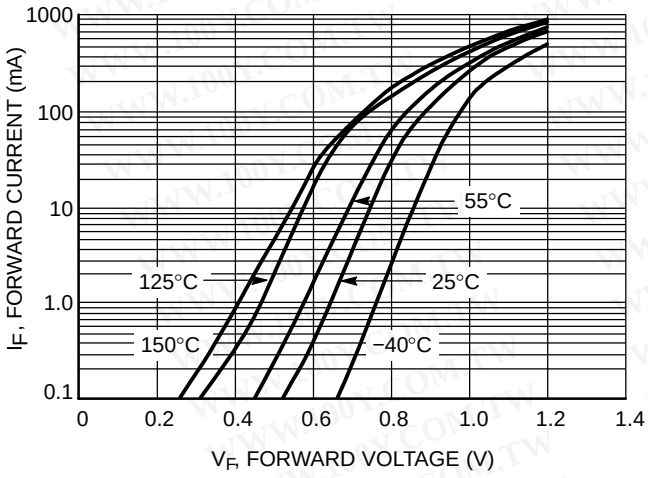


Figure 2. Forward Current

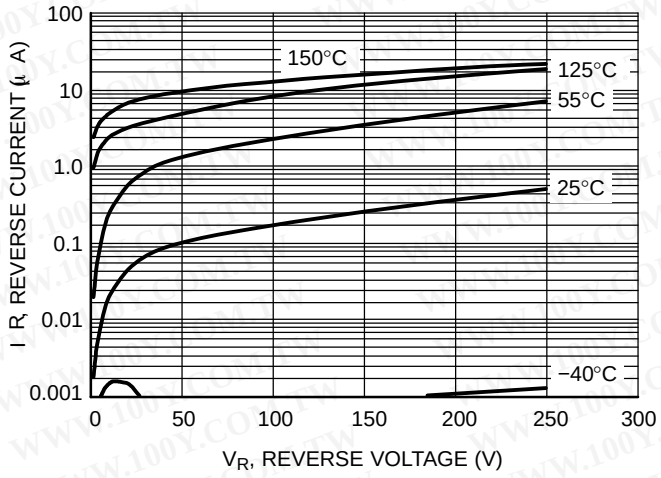


Figure 3. Leakage Current

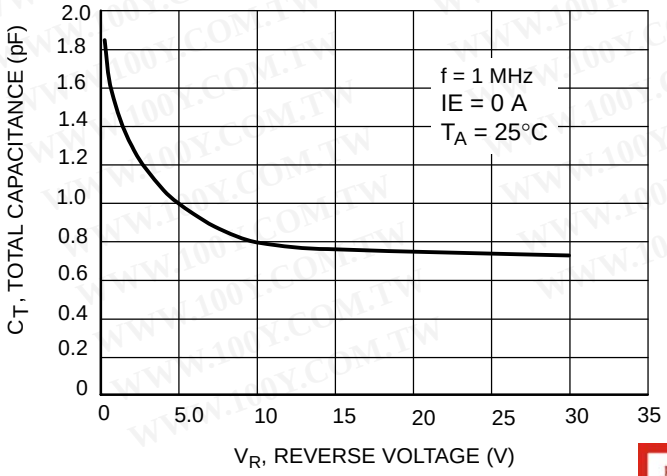
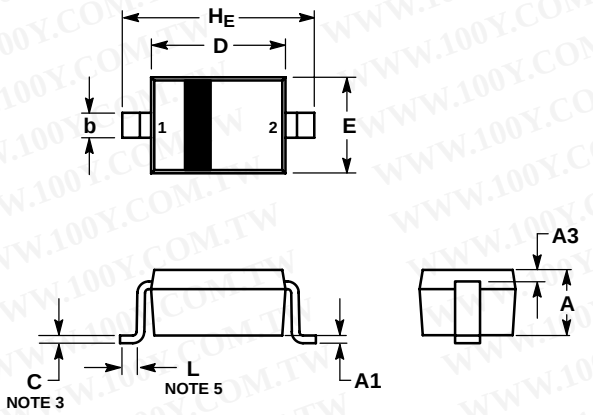


Figure 4. Total Capacitance

BAS20HT1

PACKAGE DIMENSIONS

SOD−323
CASE 477−02
ISSUE G

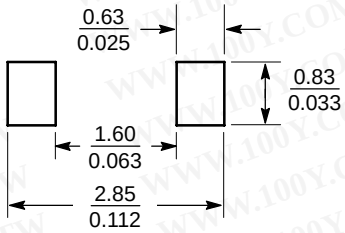


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DIMENSION L IS MEASURED FROM END OF RADIUS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.031	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3		0.15 REF			0.006 REF	
b	0.25	0.32	0.4	0.010	0.012	0.016
C	0.089	0.12	0.177	0.003	0.005	0.007
D	1.60	1.70	1.80	0.062	0.066	0.070
E	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
H_E	2.30	2.50	2.70	0.090	0.098	0.105

STYLE 1:
PIN 1. CATHODE
2. ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
Phone: 480−829−7710 or 800−344−3860 Toll Free USA/Canada
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ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

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